



February 1999

USB10H

Dual P-Channel 2.5V Specified PowerTrench™ MOSFET

General Description

These P-Channel 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

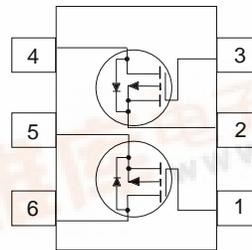
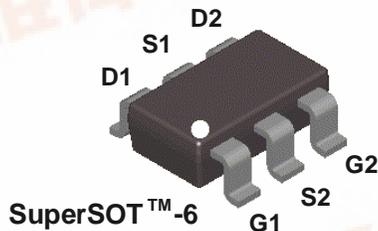
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the bigger more expensive SO-8 and TSSOP-8 packages are impractical.

Applications

- Load switch
- Battery protection
- Power management

Features

- -1.9 A, -20 V. $R_{DS(on)} = 0.170 \Omega @ V_{GS} = -4.5 V$
 $R_{DS(on)} = 0.250 \Omega @ V_{GS} = -2.5 V$
- Low gate charge (3 nC typical).
- Fast switching speed.
- High performance trench technology for extremely low $R_{DS(on)}$.
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|-----------------------------------|--|--------------------|-------|
| V _{DSS} | Drain-Source Voltage | -20 | V |
| V _{GSS} | Gate-Source Voltage | ±8 | V |
| I _D | Drain Current - Continuous (Note 1a) - Pulsed | -1.9 -5 | A |
| P _D | Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c) | 0.96 0.9 0.7 | W |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|------------------|---|-----|------|
| R _{θJA} | Thermal Resistance, Junction-to-Ambient (Note 1a) | 130 | °C/W |
| R _{θJC} | Thermal Resistance, Junction-to-Case (Note 1) | 60 | °C/W |

Package Outlines and Ordering Information

| Device Marking | Device | Reel Size | Tape Width | Quantity |
|----------------|--------|-----------|------------|------------|
| .306 | USB10H | 7" | 8mm | 3000 units |



Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|--|-----|-----|------|----------------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$ | -20 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\ \mu\text{A}$, Referenced to 25°C | | -18 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$ | | | -1 | μA |
| I_{GSSF} | Gate-Body Leakage Current, Forward | $V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$ | | | 100 | nA |
| I_{GSSR} | Gate-Body Leakage Current, Reverse | $V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$ | | | -100 | nA |

On Characteristics (Note 2)

| | | | | | | |
|--|--|---|------|-------------------------|-------------------------|----------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$ | -0.4 | -0.9 | -1.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = -250\ \mu\text{A}$, Referenced to 25°C | | 3 | | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = -4.5\text{ V}, I_D = -1.9\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -1.9\text{ A}$ @ 125°C $V_{GS} = -2.5\text{ V}, I_D = -1.7\text{ A}$ | | 0.127 0.182 0.194 | 0.170 0.270 0.250 | Ω |
| $I_{D(on)}$ | On-State Drain Current | $V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$ | -5 | | | A |
| g_{FS} | Forward Transconductance | $V_{DS} = -5\text{ V}, I_D = -1.9\text{ A}$ | | 4 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|---|--|-----|--|----|
| C_{iss} | Input Capacitance | $V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$ | | 441 | | pF |
| C_{oss} | Output Capacitance | | | 127 | | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 67 | | pF |

Switching Characteristics (Note 2)

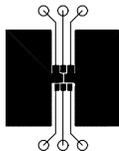
| | | | | | | |
|--------------|---------------------|--|--|-----|-----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$ | | 6 | 12 | ns |
| t_r | Turn-On Rise Time | | | 9 | 18 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 14 | 25 | ns |
| t_f | Turn-Off Fall Time | | | 3 | 9 | ns |
| Q_g | Total Gate Charge | $V_{DS} = -10\text{ V}, I_D = -1.9\text{ A},$ $V_{GS} = -4.5\text{ V}$ | | 3 | 4.2 | nC |
| Q_{gs} | Gate-Source Charge | | | 0.7 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 0.8 | | nC |

Drain-Source Diode Characteristics and Maximum Ratings

| | | | | | | |
|----------|---|---|--|------|------|---|
| I_S | Maximum Continuous Drain-Source Diode Forward Current | | | -0.8 | A | |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = -0.8\text{ A}$ (Note 2) | | -0.8 | -1.2 | V |

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. Both devices are assumed to be operating and sharing the dissipated heat energy equally.



a) 130 $^\circ\text{C/W}$ when mounted on a 0.125 in² pad of 2 oz. copper.



b) 140 $^\circ\text{C/W}$ when mounted on a 0.005 in² pad of 2 oz. copper.



c) 180 $^\circ\text{C/W}$ when mounted on a 0.0015 in² pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

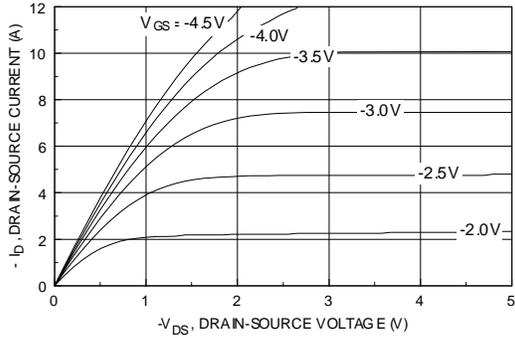


Figure 1. On-Region Characteristics.

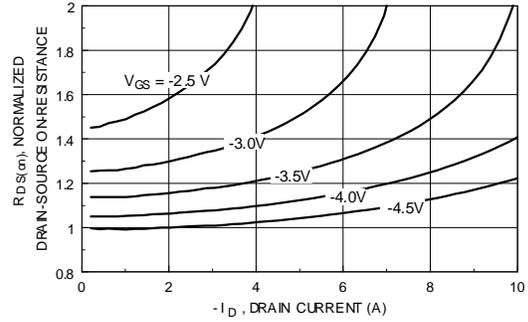


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

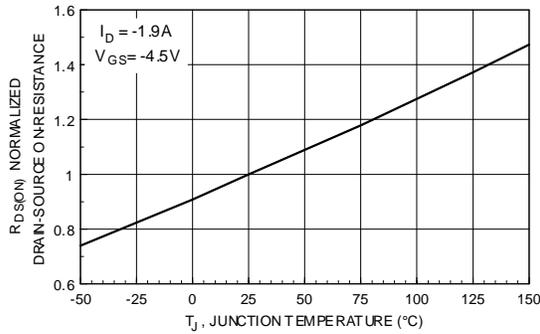


Figure 3. On-Resistance Variation with Temperature.

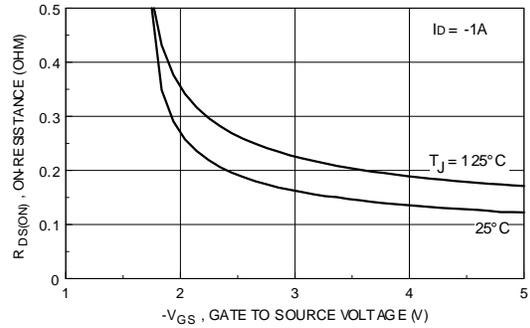


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

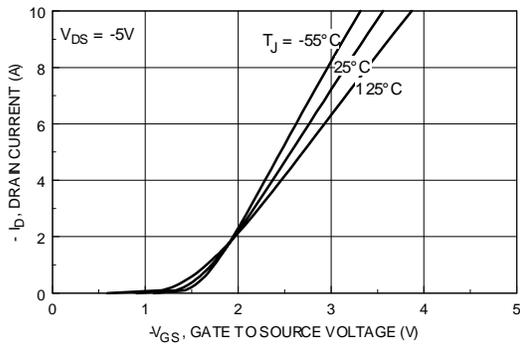


Figure 5. Transfer Characteristics.

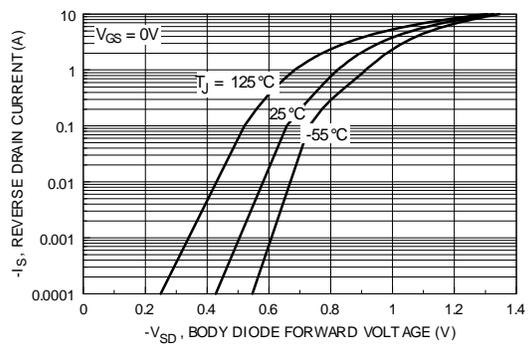


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

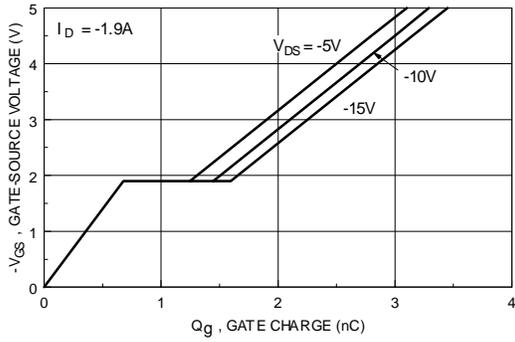


Figure 7. Gate-Charge Characteristics.

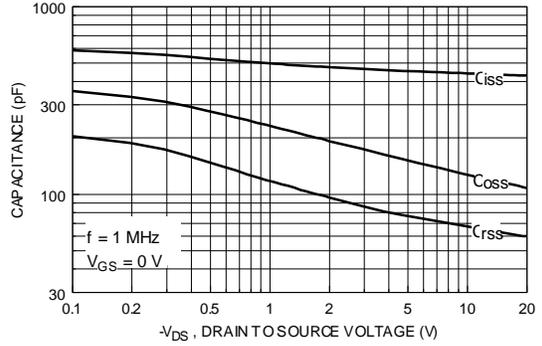


Figure 8. Capacitance Characteristics.

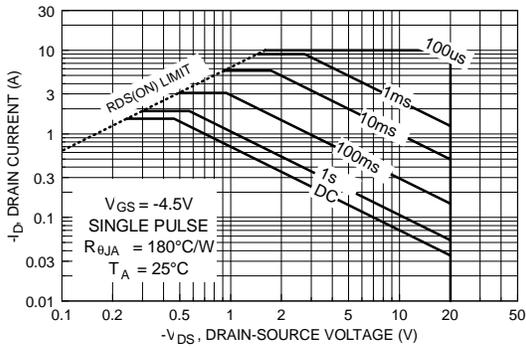


Figure 9. Maximum Safe Operating Area.

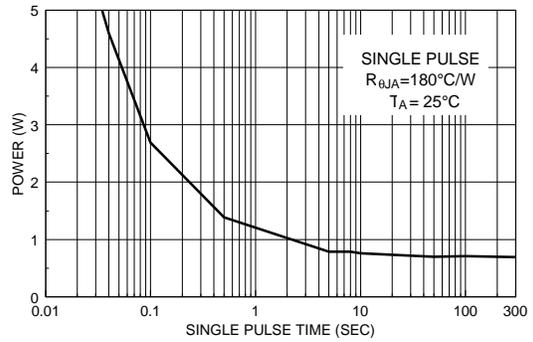


Figure 10. Single Pulse Maximum Power Dissipation.

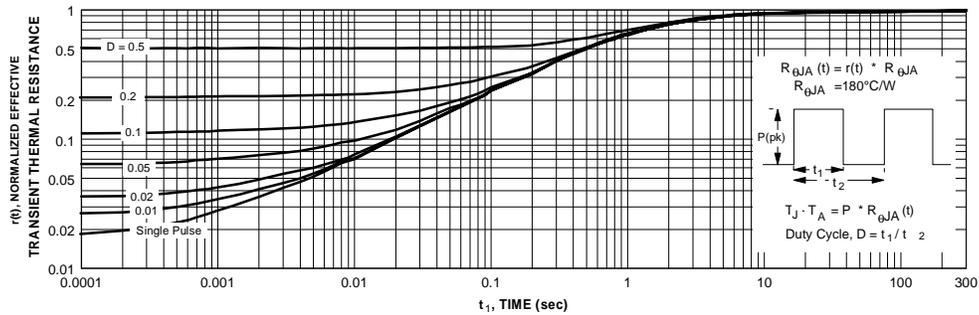


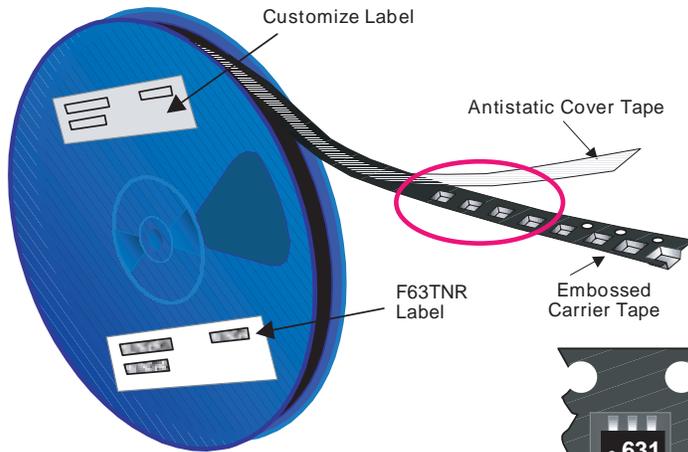
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

SuperSOT™-6 Tape and Reel Data and Package Dimensions



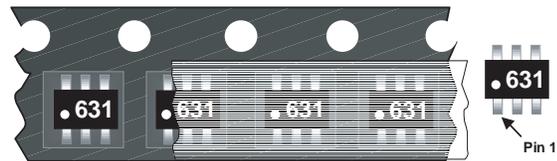
SSOT-6 Packaging Configuration: Figure 1.0



Packaging Description:

SSOT-6 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 177cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 10,000 units per 13" or 330cm diameter reel. This and some other options are described in the Packaging Information table.

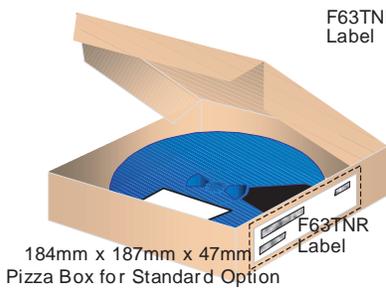
These full reels are individually barcode labeled and placed inside a pizza box (illustrated in figure 1.0) made of recyclable corrugated brown paper with a Fairchild logo printing. One pizza box contains three reels maximum. And these pizza boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



SSOT-6 Unit Orientation

| SSOT-6 Packaging Information | | |
|------------------------------|-------------------------|------------|
| Packaging Option | Standard (no flow code) | D87Z |
| Packaging type | TNR | TNR |
| Qty per Reel/Tube/Bag | 3,000 | 10,000 |
| Reel Size | 7" Dia | 13" |
| Box Dimension (mm) | 184x187x47 | 343x343x64 |
| Max qty per Box | 9,000 | 30,000 |
| Weight per unit (gm) | 0.0158 | 0.0158 |
| Weight per Reel (kg) | 0.1440 | 0.4700 |
| Note/Comments | | |

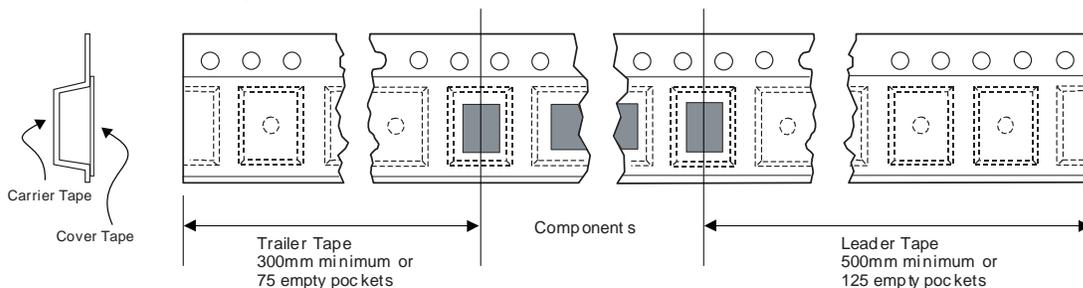
343mm x 342mm x 64mm Intermediate box for D87Z Option



F63TNR Label sample

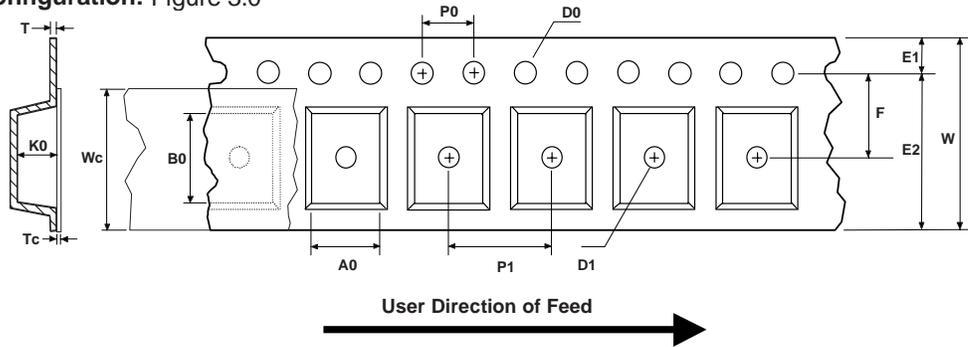


SSOT-6 Tape Leader and Trailer Configuration: Figure 2.0



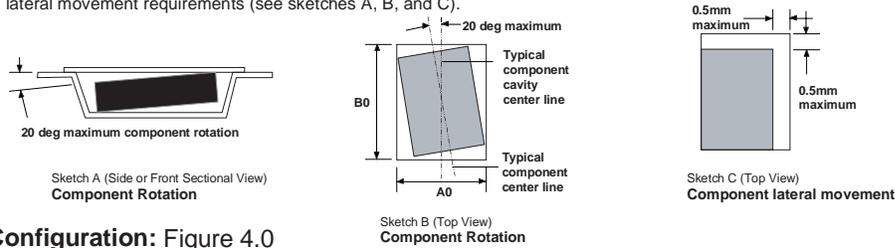
SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

SSOT-6 Embossed Carrier Tape Configuration: Figure 3.0

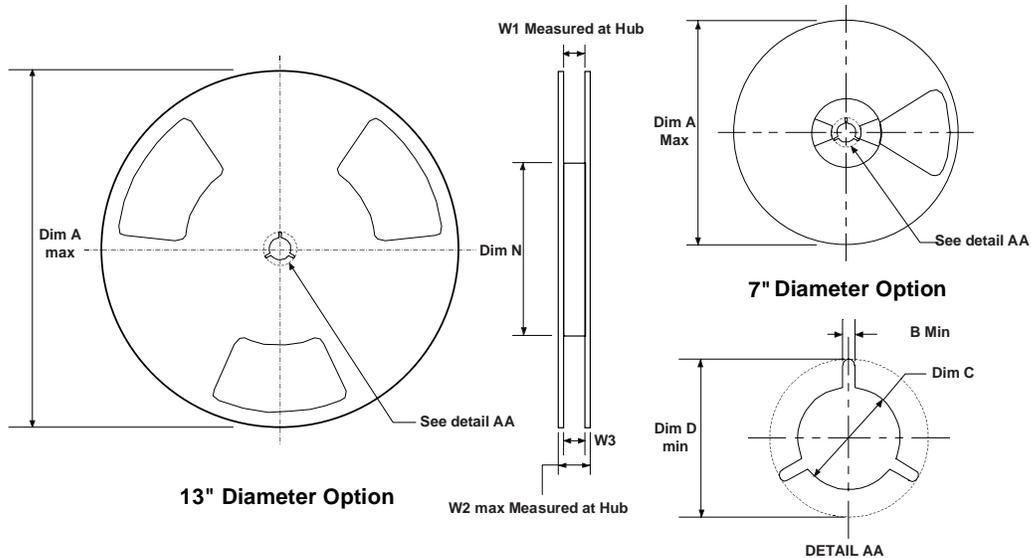


| Dimensions are in millimeter | | | | | | | | | | | | | | |
|------------------------------|---------------|---------------|-------------|---------------|-----------------|---------------|-------------|---------------|-------------|-------------|---------------|-----------------|-------------|---------------|
| Pkg type | A0 | B0 | W | D0 | D1 | E1 | E2 | F | P1 | P0 | K0 | T | Wc | Tc |
| SSOT-6 (8mm) | 3.23 ±0.10 | 3.18 ±0.10 | 8.0 ±0.3 | 1.55 ±0.05 | 1.125 ±0.125 | 1.75 ±0.10 | 6.25 min | 3.50 ±0.05 | 4.0 ±0.1 | 4.0 ±0.1 | 1.37 ±0.10 | 0.255 ±0.150 | 5.2 ±0.3 | 0.06 ±0.02 |

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



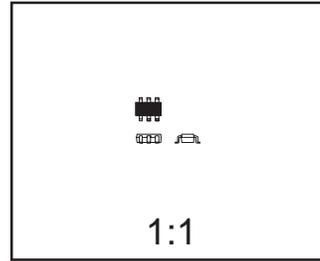
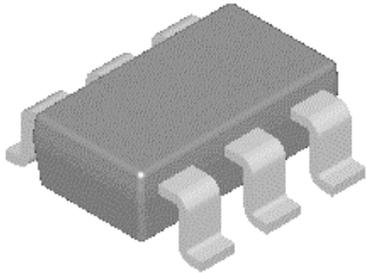
SSOT-6 Reel Configuration: Figure 4.0



| Dimensions are in inches and millimeters | | | | | | | | | |
|--|-------------|---------------|--------------|-----------------------------------|---------------|-------------|-----------------------------------|---------------|-----------------------------|
| Tape Size | Reel Option | Dim A | Dim B | Dim C | Dim D | Dim N | Dim W1 | Dim W2 | Dim W3 (LSL-USL) |
| 8mm | 7" Dia | 7.00 177.8 | 0.059 1.5 | 512 +0.020/-0.008 13 +0.5/-0.2 | 0.795 20.2 | 2.165 55 | 0.331 +0.059/-0.000 8.4 +1.5/0 | 0.567 14.4 | 0.311 - 0.429 7.9 - 10.9 |
| 8mm | 13" Dia | 13.00 330 | 0.059 1.5 | 512 +0.020/-0.008 13 +0.5/-0.2 | 0.795 20.2 | 4.00 100 | 0.331 +0.059/-0.000 8.4 +1.5/0 | 0.567 14.4 | 0.311 - 0.429 7.9 - 10.9 |

SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

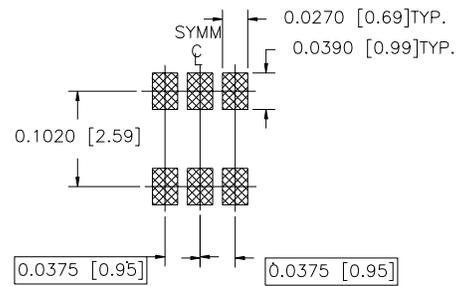
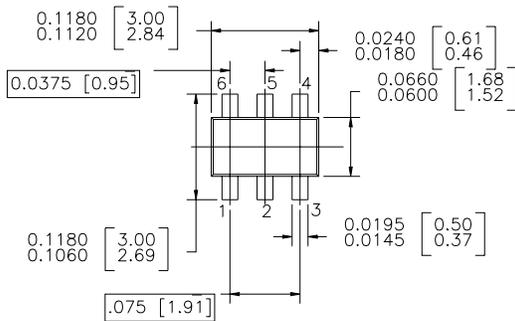
SuperSOT -6 (FS PKG Code 31, 33)



Scale 1:1 on letter size paper

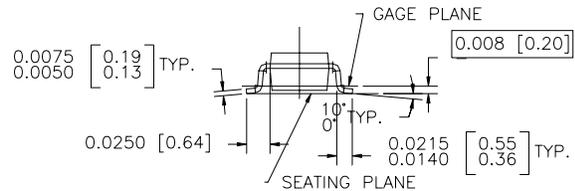
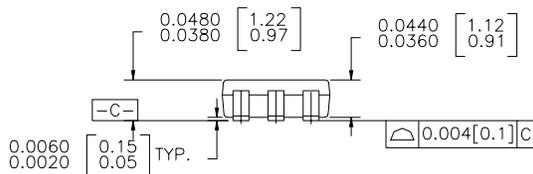
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0158



LAND PATTERN RECOMMENDATION

CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS



SUPER SOT 6 LEADS

NOTES : UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS)
MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

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| E ² CMOS™ | PowerTrench® | VCX™ |
| FACT™ | QFET™ | |
| FACT Quiet Series™ | QS™ | |
| FAST® | Quiet Series™ | |
| FASTr™ | SuperSOT™-3 | |
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